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# Switching (-30V, -5.0A)

# SP8J1

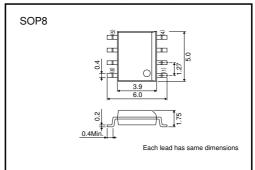
#### Features

- 1) Low On-resistance. (40m $\Omega$  at 4.5V)
- 2) High Power Package.
- 3) High speed switching.
- 4) Low voltage drive. (4.5V)

#### Applications

Power switching, DC-DC converter

## ●External dimensions (Unit : mm)



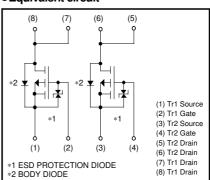
#### Structure

Silicon P-channel MOS FET

## Packaging specifications

	Package	Taping
Type	Code	ТВ
	Basic ordering unit (pieces)	2500
SP8J1		0

#### ●Equivalent circuit



### ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-30	V	
Gate-source voltage		Vgss	±20	V	
Dunin accurant	Continuous	lσ	±5.0	Α	
Drain current	Pulsed	IDP	±20	A *1	
Source current	Continuous	Is	-1.6	Α	
(Body diode)	Pulsed	Isp	-20	A *1	
Total power dissipation		PD	2.0	W *2	
Channel temperature		Tch	150	°C	
Range of Storage temperature		Tstg	-55 to +150	°C	

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	_	-	1⊕	μΑ	$V_{GS}=\pm20V$ , $V_{DS}=0V$	
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	-30	-	_	٧	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	_	1–	μΑ	V <sub>DS</sub> = -30V, V <sub>GS</sub> =0V	
Gate threshold voltage	VGS (th)	-1.0	_	2.5	٧	$V_{DS}=-10V$ , $I_{D}=-1mA$	
Static drain-source on-state resistance	R <sub>DS (on)</sub>	_	30	42	mΩ	$I_D = -5.0A$ , $V_{GS} = -10V$	*
		_	40	56	mΩ	$I_D = -2.5A$ , $V_{GS} = -4.5V$	*
		_	45	63	mΩ	$I_D = -2.5A$ , $V_{GS} = -4.0V$	*
Forward transfer admittance	Yfs	4.5	_	-	S	$V_{DS} = -10V$ , $I_{D} = -2.5A$	*
Input capacitance	Ciss	_	1400	_	pF	V <sub>DS</sub> = -10V	
Output capacitance	Coss	_	300	_	pF	V <sub>GS</sub> =0V	
Reverse transfer capacitance	Crss	_	230	_	pF	f=1MHz	
Turn-on delay time	td (on)	_	15	_	ns	I <sub>D</sub> = -2.5A	*
Rise time	tr	_	30	_	ns	V <sub>DD</sub> ≒ -15V	
Turn-off delay time	t <sub>d (off)</sub>	_	80	_	ns	V <sub>GS</sub> = -10V R <sub>L</sub> =6Ω	*
Fall time	tf	_	40	_	ns	Rgs=10Ω	*
Total gate charge	Qg	-	16	_	nC	V <sub>DD</sub> ≒−15V	
Gate-source charge	Qgs	-	3.5	_	nC	V <sub>GS</sub> = -5V	
Gate-drain charge	Q <sub>gd</sub>	_	6.5	_	nC	I <sub>D</sub> = -5.0A	

Body diode characteristics (source-drain characteristics)

Forward voltage	VSD	_	_	1.2	V	I <sub>S</sub> = -1.6A, V <sub>GS</sub> =0V



<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

#### Electrical characteristic curves

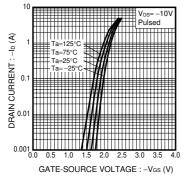


Fig.1 Typical Transfer Characteristics

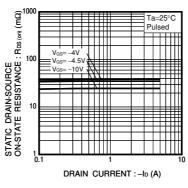


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

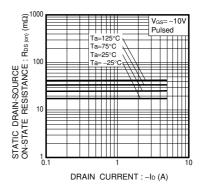


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

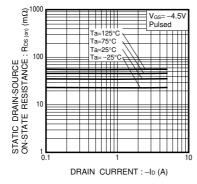


Fig.4 Static Drain-Source On-State vs. Drain Current

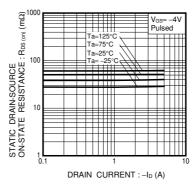


Fig.5 Static Drain-Source On-State vs. Drain Current

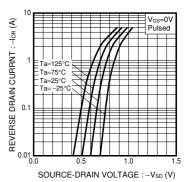


Fig.6 Reverse Drain Current Source-Drain Current

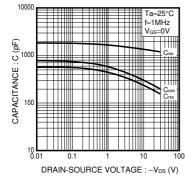


Fig.7 Typical Capacitance vs. Drain-Source Voltage

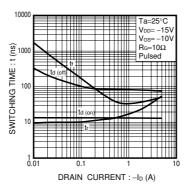


Fig.8 Switching Characteristics

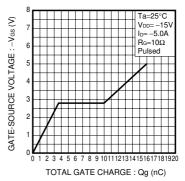


Fig.9 Dynamic Input Characteristics

#### Measurement circuits

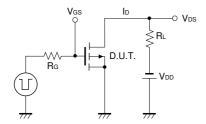


Fig.10 Switching Time Test Circuit

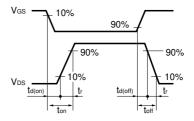


Fig.11 Switching Time Waveforms

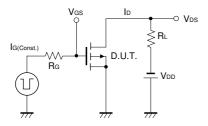


Fig.12 Gate Charge Test Circuit

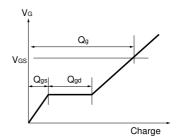


Fig.13 Gate Charge Waveform

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